

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:	§	Art Unit:	2822
Chris E. Barns et al.	§		
	§	Examiner:	Khanh B. Duong
Serial No.: 10/629,127	§		
	§	Conf. No.:	5928
Filed: July 29, 2003	§		
	§	Docket:	ITL.1016US
For: Preventing Silicide Formation at	§		P16703
the Gate Electrode in a Replacement	§		
Metal Gate Technology	§	Assignee:	Intel Corporation

Mail Stop **Amendment**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**REPLY TO DECISION ON APPEAL**

Sir:

In response to the Decision on Appeal mailed October 21, 2009, please amend the above-referenced patent application as follows:

Date of Deposit: December 10, 2009

I hereby certify that this correspondence is being electronically transmitted on the date indicated above.

  
Cynthia L. Hayden